

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

TK20J60W

• FEATURES

- Low drain-source on-resistance: $R_{DS}(ON) \le 155m_{\Omega}$
- · Easy to control Gate switching
- Enhancement mode: Vth = 2.7 to 3.7V (VDs = 10 V, ID=1mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

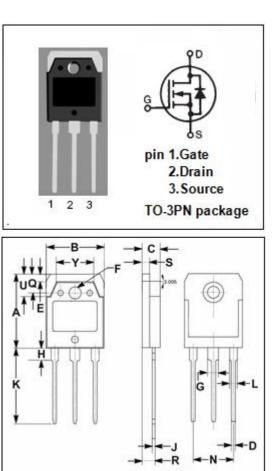
Switching Voltage Regulators

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER	VALUE	UNIT					
Drain-Source Voltage	600	V					
Gate-Source Voltage	±30	V					
Drain Current-Continuous	20	А					
Drain Current-Single Pulsed	80	А					
Total Dissipation @T _C =25°C	165	W					
Max. Operating Junction Temperature 150		°C					
Storage Temperature	-55~150	°C					
	PARAMETER Drain-Source Voltage Gate-Source Voltage Drain Current-Continuous Drain Current-Single Pulsed Total Dissipation @Tc=25°C Max. Operating Junction Temperature	PARAMETERVALUEDrain-Source Voltage600Gate-Source Voltage± 30Drain Current-Continuous20Drain Current-Single Pulsed80Total Dissipation @Tc=25°C165Max. Operating Junction Temperature150					

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.757	℃ /W	

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	m	m
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc website: www.iscsemi.cn



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ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	600			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} = 10V; I _D =1mA	2.7		3.7	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =10A			155	mΩ
lgss	Gate-Source Leakage Current	V _{GS} = ±30V;V _{DS} =0V			±1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 600V; V _{GS} = 0V			100	μA
VSDF	Diode forward voltage	I _{DR} =20 A, V _{GS} = 0 V			1.7	V

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